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Project

05-FONE-FP-008 / Device Electronics Based on Nanowires and Nanotubes (DEWINT)

Topic: Device electronics based on nanowires and nanotubes (DEWINT)

On the Role of Off-Diagonal Dephasing in Carbon Nanotube Based Photo-Detectors

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The non-equilibrium Green's function (NEGF) formalism is employed to study quantum transport in IR photo detectors based on carbon nanotube field effect transistors (CNT-FETs).

The nearest neighbor tight-binding pi-bond model is used to describe the electronic band structure. Scattering is introduced via a self-energy. For electron-phonon interaction the self-energy terms are diagonal in coordinate representation.

This local scattering approximation allows one to employ the recursive algorithm for computing the Green's functions. For electron-photon interaction the self-energy, however, contains large off-diagonal terms. We demonstrate that the usually employed local approximation the current is strongly underestimated. For accurate simulations of the photocurrent a large number of off-diagonal terms of the self-energy in coordinate representation must be taken into consideration.